

RJK6025DPE

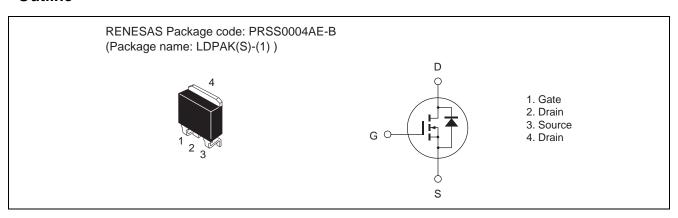
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1870-0100 Rev.1.00 Dec 08, 2009

Features

- Low on-resistance $R_{DS(on)}=13~\Omega~typ.~(at~I_D=0.4~A,~V_{GS}=10~V,~Ta=25^{\circ}C)$
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	600	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	0.8	А
Drain peak current	I _{D (pulse)} Note1	1.2	А
Body-drain diode reverse drain current	I _{DR}	0.8	А
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	1.2	Α
Channel dissipation	Pch Note2	25	W
Channel to case thermal impedance	θch-c	5	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tc = 25°C

Electrical Characteristics

 $(Ta = 25^{\circ}C)$

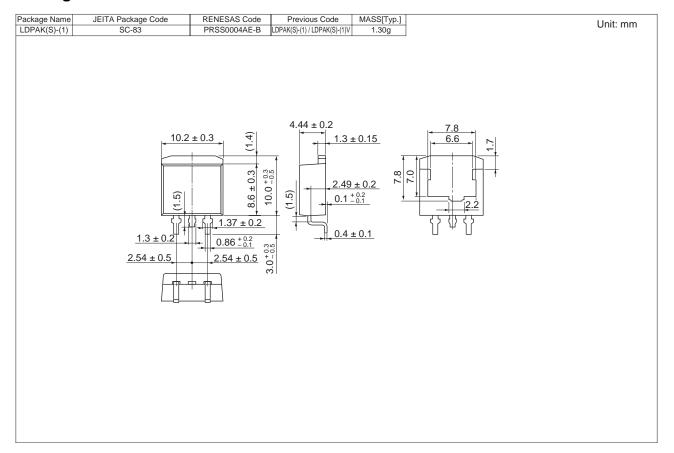
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 600 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	3	_	5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	_	13.0	17.5	Ω	$I_D = 0.4 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note3}}$
Input capacitance	Ciss	_	71.5	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	10.5	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	1.5	_	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	_	31	_	ns	I _D = 0.4 A
Rise time	t _r	_	15	_	ns	V _{GS} = 10 V
Turn-off delay time	t _{d(off)}	_	44	_	ns	$R_L = 750 \Omega$
Fall time	t _f	_	44	_	ns	$Rg = 10 \Omega$
Total gate charge	Qg	_	5.0	_	nC	V _{DD} = 480 V
Gate to source charge	Qgs	_	0.7	_	nC	V _{GS} = 10 V
Gate to drain charge	Qgd	_	3.3	_	nC	$I_D = 0.8 A$
Body-drain diode forward voltage	V_{DF}	_	0.86	1.45	V	$I_F = 0.8 \text{ A}, V_{GS} = 0^{\text{Note3}}$
Body-drain diode reverse recovery time	t _{rr}	_	157	_	ns	$I_F = 0.8 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 3. Pulse test

^{4.} This device is sensitive to electrostatic discharge.

It is recommended to adopt appropriate cautions when handling this product.

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK6025DPE-00-J3	1000 pcs	Taping

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